

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

SIHG47N60AEF

• FEATURES

- With TO-247 packaging
- · With low gate drive requirements
- · Easy to drive
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

C

APPLICATIONS

Switching applications

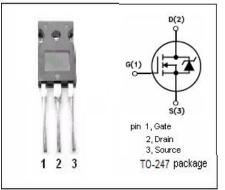
• ABSOLUTE MAXIMUM RATINGS(Ta=25 C)								
SYMBOL	PARAMETER	VALUE	UNIT					
V _{DSS}	Drain-Source Voltage	600	V					
V _{GSS}	Gate-Source Voltage	±30	∧v					
lo	Drain Current-Continuous;@Tc=25℃ Tc=100℃	43 27	A					
I _{DM}	Drain Current-Single Pulsed	130	А					
P _D	Total Dissipation	313	W					
Tj	Operating Junction Temperature	-55~150	°C					
T _{stg}	Storage Temperature	-55~150	°C					

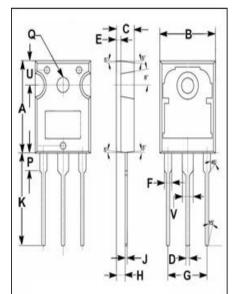
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

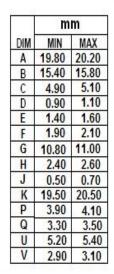
• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.4	°C /W

1







isc website: www.iscsemi.cn

isc N-Channel MOSFET Transistor

SIHG47N60AEF

ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	600			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =0.25mA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =24A		56	65	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V;@Tc=25℃ V _{DS} = 480V; V _{GS} = 0V;Tc=125℃			1 10	μA
VSDF	Diode forward voltage	I _{SD} =24A, V _{GS} = 0 V			1.2	V



NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications. ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

2